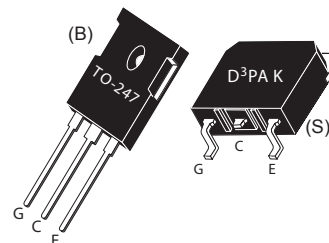



Ultra Fast NPT - IGBT®

The Ultra Fast NPT - IGBT® family of products is the newest generation of planar IGBTs optimized for outstanding ruggedness and the best trade-off between conduction and switching losses.



Features

- Low Saturation Voltage
- Low Tail Current
- RoHS Compliant 
- Short Circuit Withstand Rated
- High Frequency Switching
- Ultra Low Leakage Current

Unless stated otherwise, Microsemi discrete IGBTs contain a single IGBT die. This device is recommended for applications such as induction heating (IH), motor control, general purpose inverters and uninterruptible power supplies (UPS).



MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	Ratings	Unit
V_{ces}	Collector Emitter Voltage	1200	V
V_{GE}	Gate-Emitter Voltage	± 30	
I_{C1}	Continuous Collector Current @ $T_C = 25^\circ\text{C}$	75	A
I_{C2}	Continuous Collector Current @ $T_C = 125^\circ\text{C}$	25	
I_{CM}	Pulsed Collector Current ^①	100	
SCWT	Short Circuit Withstand Time: $V_{CE} = 600V, V_{GE} = 15V, T_C = 125^\circ\text{C}$	10	μs
P_D	Total Power Dissipation @ $T_C = 25^\circ\text{C}$	521	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ\text{C}$
T_L	Max. Lead Temp. for Soldering: 0.063" from Case for 10 Sec.	300	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Min	Typ	Max	Unit
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage ($V_{GE} = 0V, I_C = 500\mu\text{A}$)	1200			Volts
$V_{GE(TH)}$	Gate Threshold Voltage ($V_{CE} = V_{GE}, I_C = 1.0\text{mA}, T_J = 25^\circ\text{C}$)	3.5	5.0	6.5	
$V_{CE(ON)}$	Collector-Emitter On Voltage ($V_{GE} = 15V, I_C = 25A, T_J = 25^\circ\text{C}$)		2.5	3.2	
	Collector-Emitter On Voltage ($V_{GE} = 15V, I_C = 25A, T_J = 125^\circ\text{C}$)		3.3		
	Collector-Emitter On Voltage ($V_{GE} = 15V, I_C = 50A, T_J = 25^\circ\text{C}$)		3.5		
I_{CES}	Collector Cut-off Current ($V_{CE} = 1200V, V_{GE} = 0V, T_J = 25^\circ\text{C}$) ^②		5	500	μA
	Collector Cut-off Current ($V_{CE} = 1200V, V_{GE} = 0V, T_J = 125^\circ\text{C}$) ^②		50		
I_{GES}	Gate-Emitter Leakage Current ($V_{GE} = \pm 20V$)			± 250	nA

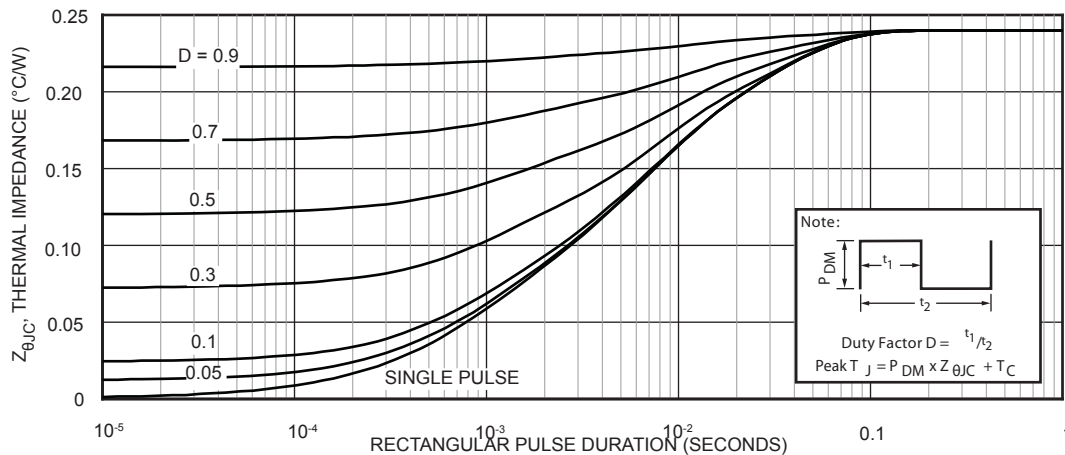
 **CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.**

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	Capacitance $V_{GE} = 0V, V_{CE} = 25V$ $f = 1MHz$		2784		pF
C_{oes}	Output Capacitance			271		
C_{res}	Reverse Transfer Capacitance			75		
V_{GEP}	Gate to Emitter Plateau Voltage	Gate Charge $V_{GE} = 15V$ $V_{CE} = 600V$ $I_C = 25A$		7.5		V
$Q_g^{(3)}$	Total Gate Charge			154	203	
Q_{ge}	Gate-Emitter Charge			20	27	
Q_{gc}	Gate- Collector Charge			76	97	
$t_{d(on)}$	Turn-On Delay Time	Inductive Switching (25°C) $V_{CC} = 600V$ $V_{GE} = 15V$ $I_C = 25A$ $R_G = 4.3 \Omega^{(4)}$ $T_J = +25^\circ C$		16		ns
t_r	Current Rise Time			10		
$t_{d(off)}$	Turn-Off Delay Time			122		
t_f	Current Fall Time			20		
$E_{on2}^{(5)}$	Turn-On Switching Energy	Inductive Switching (25°C) $V_{CC} = 600V$ $V_{GE} = 15V$ $I_C = 25A$ $R_G = 4.3 \Omega^{(4)}$ $T_J = +25^\circ C$		742	1110	μJ
$E_{off}^{(6)}$	Turn-Off Switching Energy			427	640	
$t_{d(on)}$	Turn-On Delay Time	Inductive Switching (125°C) $V_{CC} = 600V$ $V_{GE} = 15V$ $I_C = 25A$ $R_G = 4.3 \Omega^{(4)}$ $T_J = +125^\circ C$		16		ns
t_r	Current Rise Time			10		
$t_{d(off)}$	Turn-Off Delay Time			136		
t_f	Current Fall Time			28		
$E_{on2}^{(5)}$	Turn-On Switching Energy	Inductive Switching (125°C) $V_{CC} = 600V$ $V_{GE} = 15V$ $I_C = 25A$ $R_G = 4.3 \Omega^{(4)}$ $T_J = +125^\circ C$		1297	1945	μJ
$E_{off}^{(6)}$	Turn-Off Switching Energy			480	720	

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic	Min	Typ	Max	Unit
$R_{\theta JC}$	Junction to Case Thermal Resistance			.24	°C/W
$R_{\theta JA}$	Junction to Ambient Thermal Resistance			40	
W_T	Package Weight		.22		oz
			6.2		g
Torque	Mounting Torque (TO-247 Package), 4-40 or M3 screw			10	in-lbf
				6.2	N·m

- 1 Repetitive Rating: Pulse width and case temperature limited by maximum junction temperature.
 - 2 Pulse test: Pulse Width < 380μs, duty cycle < 2%.
 - 3 See Mil-Std-750 Method 3471.
 - 4 R_G is external gate resistance, not including internal gate resistance or gate driver impedance. (MIC4452)
 - 5 E_{on2} is the clamped inductive turn on energy that includes a commutating diode reverse recovery current in the IGBT turn on energy loss. A combi device is used for the clamping diode.
 - 6 E_{off} is the clamped inductive turn-off energy measured in accordance with JEDEC standard JESD24-1.
- Microsemi reserves the right to change, without notice, the specifications and information contained herein.



TYPICAL PERFORMANCE CURVES

APT25GR120B_S

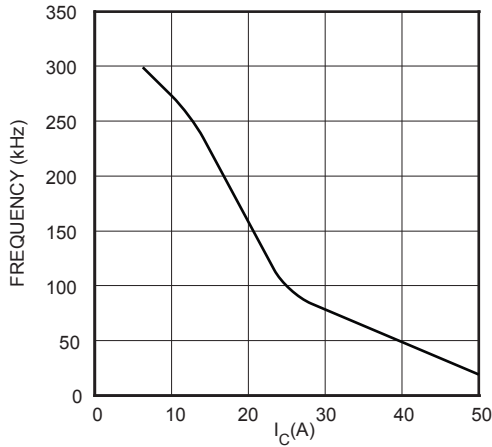


FIGURE 2, Max Frequency vs Current ($T_{case} = 75^{\circ}C$)

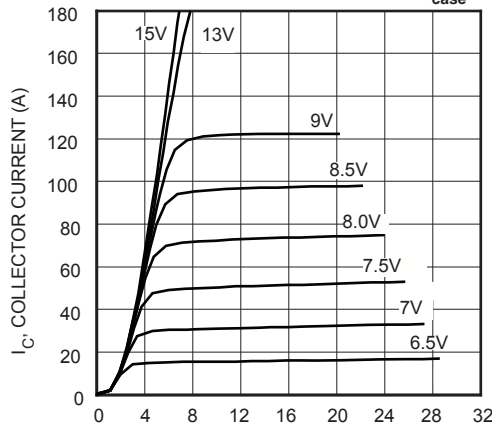


FIGURE 4, Output Characteristics ($T_J = 25^{\circ}C$)

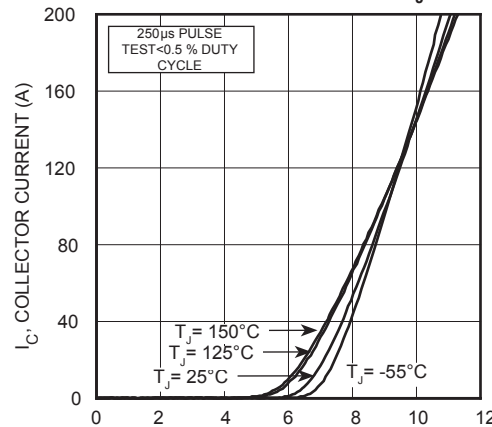


FIGURE 6, Transfer Characteristics

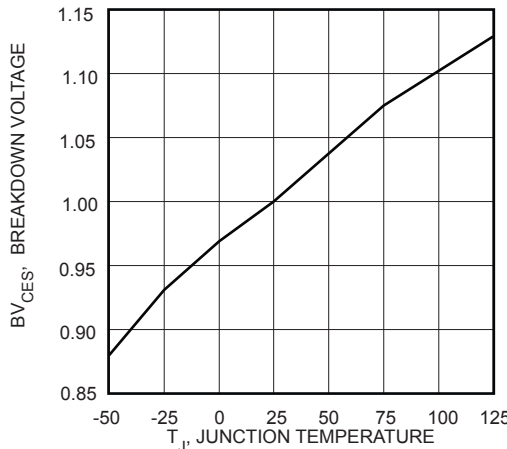


FIGURE 8, Breakdown Voltage vs Junction Temperature

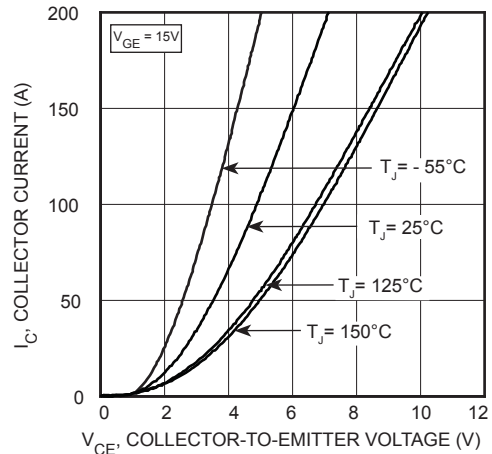


FIGURE 3, Saturation Voltage Characteristics ($T_J = 25^{\circ}C$)

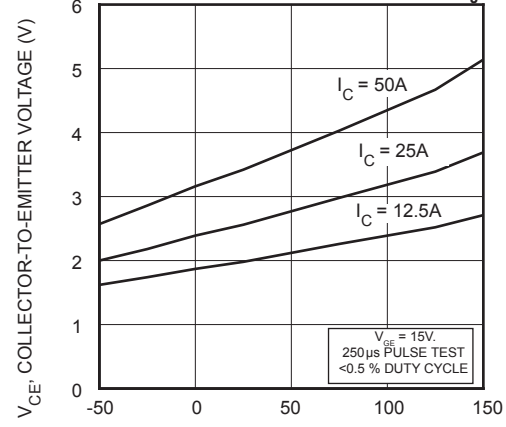


FIGURE 5, On State Voltage vs Junction Temperature

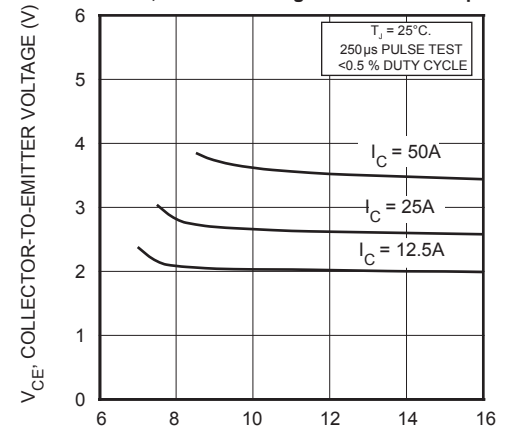


FIGURE 7, On State Voltage vs Gate-to-Emitter Voltage

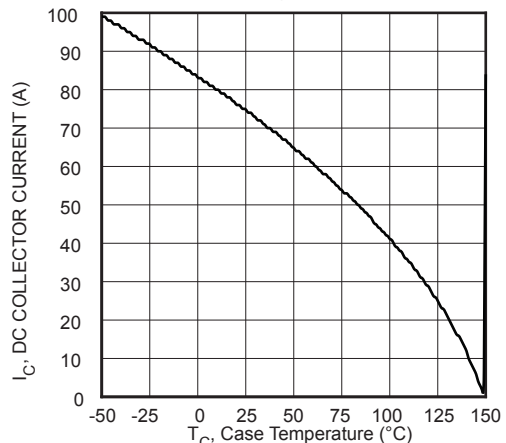


FIGURE 9, DC Collector Current vs Case Temperature

TYPICAL PERFORMANCE CURVES

APT25GR120B_S

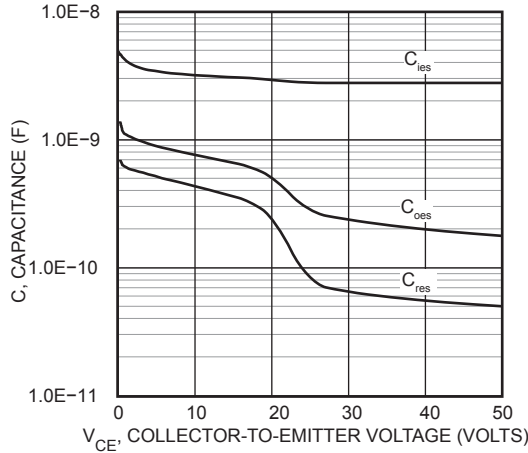


FIGURE 10, Capacitance vs Collector-To-Emitter Voltage

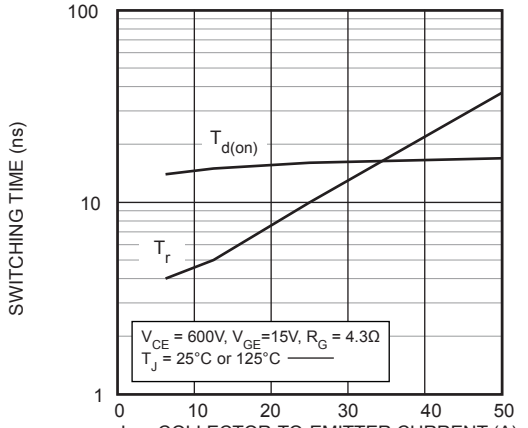


FIGURE 12, Turn-On Time vs Collector Current

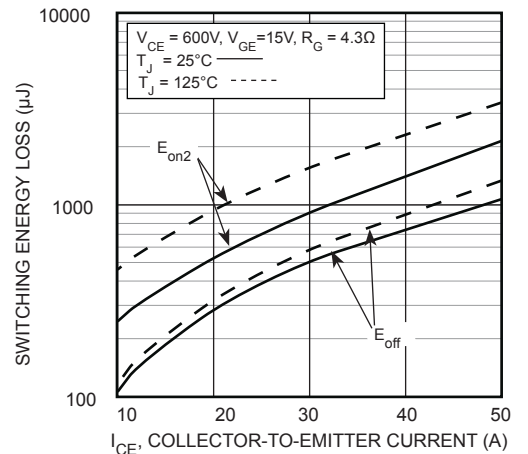


FIGURE 14, Energy Loss vs Collector Current

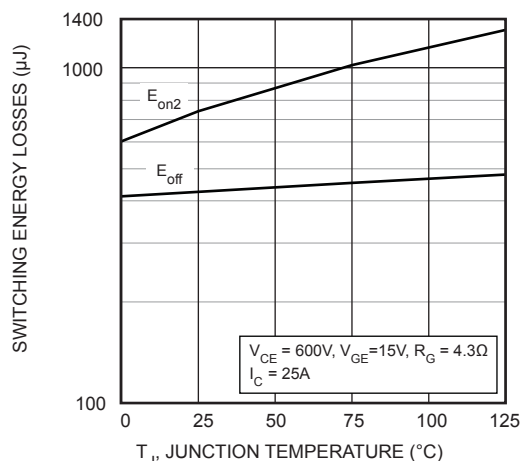


FIGURE 16, Switching Energy vs Junction Temperature

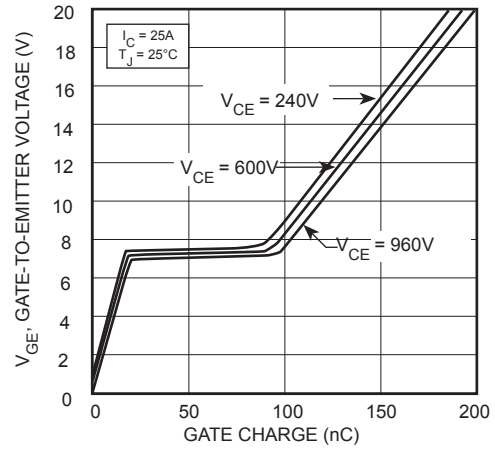


FIGURE 11, Gate charge

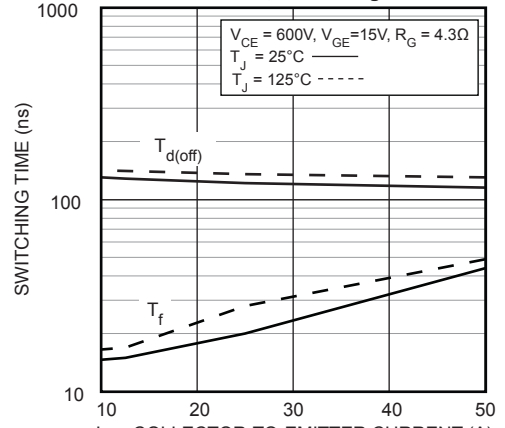


FIGURE 13, Turn-Off Time vs Collector Current

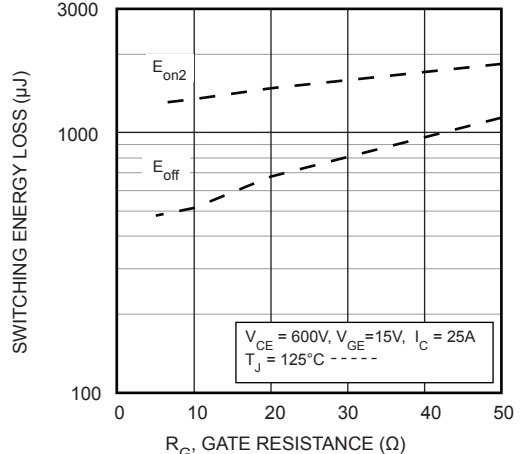


FIGURE 15, Energy Loss vs Gate Resistance

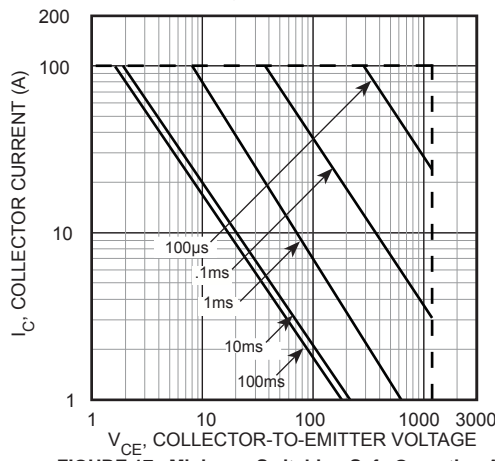
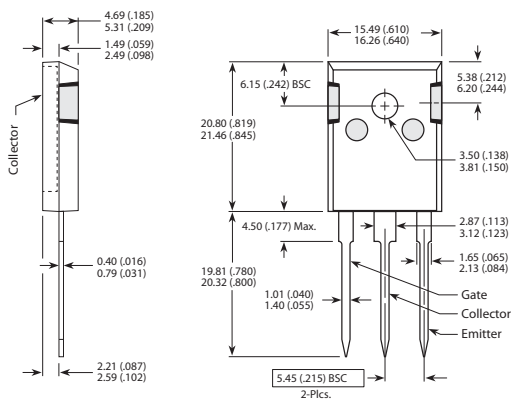


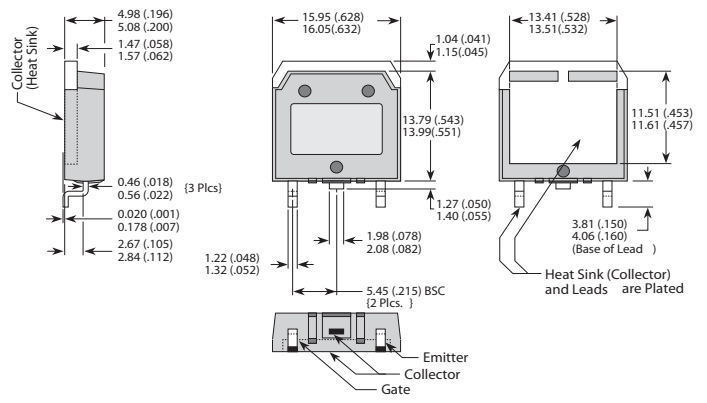
FIGURE 17, Minimum Switching Safe Operating Area

TO-247 Package Outline



Dimensions in Millimeters (Inches)

D³PAK Package Outline



Dimensions in Millimeters (Inches)